

An experimental study of diffusion welded contacts to p-type silicon carbide

Korolkov, Oleg Telekommunikatsioon 2002 : IX rahvusvahelise telekommunikatsioonipäeva materjalid 2002 / lk. 21-23 : ill

Analysis of deep level centers in GaAs pin-diode structures

Korolkov, Oleg; Toompuu, Jana; Rang, Toomas Elektronika ir elektrotehnika = Electronics and electrical engineering 2013 / [4 p.] : ill

Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures

Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas Materials characterization VII 2015 / p. 283-294 : ill

Analysis of the basic Schottky parameters for diffusion-welded aluminium contacts to p- and n-type SiC

Korolkov, Oleg; Ljutov, Jevgeni; Kuznetsova, Natalja; Ruut, Jana; Rang, Toomas BEC 2004 : proceedings of the 9th Biennial Baltic Electronics Conference : October 3-6, 2004, Tallinn, Estonia 2004 / p. 51-53 : ill

Change in the parameters of electron-irradiated 4H-SiC schottky diodes as a function of the time during low-temperature isothermal annealing

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; Toompuu, Jana; Sleptsuk, Natalja; Rang, Toomas Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 734-737 <https://doi.org/10.4028/www.scientific.net/MSF.963.734> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Clamp mode package diffusion welded power SiC Schottky diodes

Korolkov, Oleg; Kuznetsova, Natalja; Rang, Toomas BEC 2006 : 2006 International Baltic Electronics Conference : Tallinn University of Technology, October 2-4, 2006, Tallinn, Estonia : proceedings of the 10th Biennial Baltic Electronics Conference 2006 / p. 55-58 : ill

Comparative characteristics of 6H- and 4H-SiC surfaces in diffusion welding

Korolkov, Oleg; Rang, Toomas Proceedings of the Estonian Academy of Sciences. Engineering 2001 / 4, p. 347-353 : ill

Comparative characteristics of diffusion welded Al contacts to 6H- and 4H-SiC substrates

Korolkov, Oleg; Rang, Toomas The 7th Biennial Conference on Electronics and Microsystem Technology "Baltic Electronics Conference" : BEC 2000 : October 8 - 11, 2000, Tallinn, Estonia : conference proceedings 2000 / p. 23-26 : ill

Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

Sleptšuk, Natalja; Korolkov, Oleg; Land, Raul; Toompuu, Jana; Annus, Paul; Rang, Toomas BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 39-42 : ill http://www.ester.ee/record=b2150914*est

Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

Sleptšuk, Natalja; Lebedev, Alexander A.; Eliseyev, Ilya; Korolkov, Oleg; Toompuu, Jana; Land, Raul; Mikli, Valdek; Zubov, Alexander; Rang, Toomas Modern Materials and Manufacturing 2019 : 12th International DAAAM Baltic Conference and 27th International Baltic Conference BALTMATTRIB 2019. Selected, peer reviewed papers from the conference Modern Materials and Manufacturing 2019 (MMM 2019), April 24-26, 2019, Tallinn, Estonia 2019 / p. 185-190 : ill https://www.ester.ee/record=b5235278*est <https://www.scientific.net/KEM.799.185> <https://doi.org/10.4028/www.scientific.net/KEM.799.185> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

Kozlovski, Vitali V.; Korolkov, Oleg; Lebedev, Alexander A.; Toompuu, Jana; Sleptsuk, Natalja Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 <https://doi.org/10.4028/www.scientific.net/MSF.1004.231> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

Comparison of individual SiC JBS chips and JBS stacks connected in series by diffusion welding

Sleptšuk, Natalja; Korolkov, Oleg; Toompuu, Jana; Rang, Toomas BEC 2010 : 2010 12th Biennial Baltic Electronics Conference : proceedings of the 12th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 4-6, 2010, Tallinn, Estonia 2010 / p. 81-84 : ill

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.447>

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

Lebedev, Alexander A.; Davydovskaya, Klavdia S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 730-733 <https://doi.org/10.4028/www.scientific.net/MSF.963.730> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Diffusion welded Al contacts to p-type SiC

Korolkov, Oleg; Rang, Toomas; Syrkin, A.; Dmitriev, V. Silicon Carbide and Related Materials 2002 : ECSCRM2002 2003 / p. 697-700

Diffusion welded contacts and related art applied to semiconductor materials

Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Elektronika ir elektrotehnika = Electronics and electrical engineering 2011 / p. 67-70 : ill <https://eejournal.ktu.lt/index.php/elt/article/view/359>

Diffusion welded contacts for silicon semiconductor devices

Korolkov, Oleg; Rang, Toomas Proceedings of the International Conference and Exhibition Micro Materials : MicroMat '97, April 16-18, 1997, Berlin, Germany 1997 / p. 1035-1037

Diffusion welding contacts to 6H-SiC substrates

Korolkov, Oleg; Rang, Toomas 43. Internationales Wissenschaftliches Kolloquium, 21.-24.09.1998 1998 / p. 47-48

Diffusion welding techniques for power SiC Schottky packaging

Korolkov, Oleg; Rang, Toomas; Syrkin, A.; Dmitriev, V. Final programm of the 12th International Conference on Silicon Carbide and Related Materials : ICSCRM2005 : Pittsburgh, PA, USA 2005 / p. 71

Diffusion welding techniques for power SiC Schottky packaging

Korolkov, Oleg; Rang, Toomas; Syrkin, A.; Dmitriev, V. Silicon carbide and related materials 2005 2006 / p. 919-922

Diffusion welding technology as a method of metallization of ceramic substrates

Korolkov, Oleg; Rang, Toomas BEC'96 : the 5th Biennial Baltic Electronics Conference, October 7-11, 1996, Tallinn, Estonia : proceedings 1996 / p. 479-482: ill

Diffusion welding technology for 6H-SiC substrates

Korolkov, Oleg; Rang, Toomas BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 251-252: ill

Diffusion welding technology for wide bandgap materials

Rang, Toomas; Korolkov, Oleg Proceedings of the European COPEX Seminar, June 17-19, 1997, Vienna, Austria 1997 / p. 124-127

DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions

Ivanov, Pavel; **Korolkov, Oleg**; Samsonova, Tatyana; **Sleptšuk, Natalja**; Potapov, Alexander; **Toompuu, Jana; Rang, Toomas** Materials science forum 2011 / p. 409-412

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg; Sleptšuk, Natalja** Semiconductors 2011 / p. 1306-1310 : ill <https://doi.org/10.1134/S1063782611100101>

Electron microscopy study of contact layers in n-type 4H-SiC after diffusion welding

Korolkov, Oleg; Sleptšuk, Natalja; Sitnikova, A.; **Rang, Toomas** BEC 2008 : 2008 International Biennial Baltic Electronics Conference : proceedings of the 11th Biennial Baltic Electronics Conference : Tallinn University of Technology : October 6-8, 2008, Tallinn, Estonia 2008 / p. 91-94 : ill

Experimental study of surface distortions in silicon carbide caused by diffusion welding

Mizsei, Janos; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas** BEC 2012 : 2012 13th Biennial Baltic Electronics Conference : proceedings of the 13th Biennial Baltic Electronics Conference : October 3-5, 2012, Tallinn, Estonia 2012 / p. 53-56 : ill

Formation of Diffusion welded Al contacts to semiconductor silicon carbide

Korolkov, Oleg 2004

Formation of large area Al contacts on 6H- and 4H-SiC substrates

Korolkov, Oleg; Rang, Toomas Abstracts of the 3rd European Conference on Silicon Carbide and Related Materials : ECSCRM'2000 : Sept. 3-7, 2000, Kloster Banz, Germany 2000 / p. 188

Formation of large area Al contacts on 6H- and 4H-SiC substrates

Korolkov, Oleg; Rang, Toomas Silicon Carbide and Related Materials : ECSCRM2000 : proceedings of the 3rd European Conference on Silicon Carbide and Related Materials : Kloster Banz, Germany, September 2000 2001 / p. 603-606 : ill

GaAs based diffusion welded high voltage diode stacks [Electronic resource]

Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Voitovitš, Viktor; Rang, Toomas IEEE International Conference on Semiconductor Electronics CD-ROM Proceedings 2010 / [4] p

High quality metal ceramic interfaces using diffusion welding technology

Korolkov, Oleg; Rang, Toomas Proceedings of the ASDAM'96, Oct. 20-24, 1996, Bratislava, Slovakia 1996 / p. 309-312

High voltage diffusion welded stacks on the basis of SiC Schottky diodes

Korolkov, Oleg; Sleptšuk, Natalja; Annus, Paul; Land, Raul; Rang, Toomas ICSRM 2015 : program guide 2015 / p. 73

High-voltage diffusion welded stacks on the basis of SiC Schottky diodes

Korolkov, Oleg; Sleptšuk, Natalja; Annus, Paul; Land, Raul; Rang, Toomas Silicon carbide and related materials 2015 (ICSRM 2015) : selected, peer reviewed papers from the 16th International Conference on Silicon Carbide and Related Materials, October 4-9, 2015, Giardini Naxos, Italy 2016 / p. 790-794 : ill <http://dx.doi.org/10.4028/www.scientific.net/MSF.858.790>

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

Kozlovski, Vitali V.; Korolkov, Oleg; Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshtein, Michael E.; Sleptšuk, Natalja; Strel'Chuk, Anatolii M.; Toompuu, Jana Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244>
[Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Interpretation of some physical parameters of SiC Schottky interfaces manufactured by diffusion welding technology

Rang, Toomas; Korolkov, Oleg; Ljutov, Jevgeni Proceedings of the Estonian Academy of Sciences. Engineering 2004 / 3, p. 179-184

Investigation of additional states in the silicon carbide surface after diffusion welding

Mizsei, Janos; Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas ICSCRM2011 : Cleveland Ohio, USA, September 11-16, 2011 : abstracts 2011 / p. 356 : ill

Investigation of deep level centers in i- and n-layers of GaAs pin-diodes

Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Rang, Toomas BEC 2014 : 2014 14th Biennial Baltic Electronics Conference : proceedings of the 14th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 6-8, 2014, Tallinn, Estonia 2014 / p. 25-28 : ill

Investigation of p-i-n GaAs structures by DLTS method

Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Rang, Toomas Elektronika ir elektrotehnika = Electronics and electrical engineering 2010 / 4, p. 51-54 : ill

Investigation of subcontact layers in SiC after diffusion welding

Korolkov, Oleg; Kuznetsova, Natalja; Sitnikova, A.; Viljus, Mart; Rang, Toomas Silicon carbide and related materials 2007 2009 / p. 647-650

Investigation of subcontact layers in SiC after diffusion welding

Korolkov, Oleg; Kuznetsova, Natalja; Sitnikova, A.; Viljus, Mart; Rang, Toomas Silicon carbide and related materials 2007 / p. 100 <https://www.scientific.net/MSF.600-603.647>

Investigation of the combined stress and strain situation in diffusion welded rectifying elements

Korolkov, Oleg; Rang, Toomas; Kurel, Raido Surface treatment VI 2003 / p. 307-316 <https://www.witpress.com/elibrary/wit-transactions-on-engineering-sciences/39/1441>

Investigation of the graphene-on-silicon-carbide and CVD graphene as a basis for bioimpedance sensor applications : poster

Sleptšuk, Natalja; Land, Raul; Toompuu, Jana; Lebedev, Alexander A.; Davydov, Valery; Eliseyev, Ilya; Kalinina, Evgenia; Korolkov, Oleg; Rang, Toomas ePosters 2018 / 1 p.: ill <https://cdn.technologynetworks.com/ep/pdfs/natalja-sleptuk-a-raul-land-a-jana-toompuu-a-alexander-lebedev-b-valery-davydov-b-ilya-eliseyev-b.pdf>

Investigation of the intermediate layer in the metal-silicon carbide contact obtained by diffusion welding = Difusioonkeevitusega valmistatud metalli ja ränikarbiidi vahelise ülemineku kvaliteet uurimine

Sleptšuk, Natalja 2011 https://www.ester.ee/record=b2692547*est

Large area 4H-SiC power Schottky diode

Rang, Toomas; Korolkov, Oleg; Pikkov, Mihhail Abstracts of the 3rd International Conference and Exhibition Micro Materials : MicroMat2000 : April 17-19, 2000, Berlin, Germany 2000 / p. 303-304

Large area 4H-SiC power Schottky diode

Rang, Toomas; Korolkov, Oleg; Pikkov, Mihhail Proceedings of the 3rd International Conference and Exhibition Micro Materials : MicroMat2000 : April 17-19, 2000, Berlin, Germany 2000 / p. 890-893

Large area 6H-SiC Schottky diode

Rang, Toomas; Korolkov, Oleg; Pikkov, Mihhail Proceedings of the Estonian Academy of Sciences. Engineering 2000 / 2, p. 155-159 : ill https://artiklid.elnet.ee/record=b1004045*est

Large area high quality interfaces to SiC substrates - technology and modelling

Rang, Toomas; Korolkov, Oleg; Kurel, Raido; Pikkov, Mihhail Materials mechanics, fracture mechanics, micro mechanics 1999 / p. 574-579: ill

Leakage currents in 4H-SiC JBS diodes

Ivanov, Pavel; Korolkov, Oleg; Sleptšuk, Natalja Semiconductors 2012 / p. 397-400 : ill
<https://link.springer.com/article/10.1134/S106378261203013X>

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Semiconductors 2019 / p. 975-978 <https://doi.org/10.1134/S1063782619070133> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Metallization technologies for wide band-gap semiconductor substrates : (invited paper)

Rang, Toomas; Korolkov, Oleg; Pikkov, Mihhail Proceedings of the 6th Nexspan Workshop Microsystems Technology Activities in Baltic Region : 23-24 April, 1999, Vilnius, Lithuania 1999 / p. 27-30

Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill http://www.ester.ee/record=b2150914*est

Polytypic heterojunctions for wide bandgap semiconductor materials

Shenkin, Mikhail; Korolkov, Oleg; Rang, Toomas; Rang, Galina Materials characterization VII 2015 / p. 273-282 : ill

Preliminary investigation of diffusion welded contacts to p-type 6H-SiC

Korolkov, Oleg; Rang, Toomas; Kuznetsova, Natalja; Ruut, Jana BEC 2002 : proceedings of the 8th Biennial Baltic Electronics Conference : October 6-9, 2002, Tallinn, Estonia 2002 / p. 55-56 : ill

SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack

Korolkov, Oleg; Land, Raul; Toompuu, Jana; Sleptšuk, Natalja; Rang, Toomas Silicon carbide and related materials 2017 : ICSCRM 2017 : selected, peer reviewed papers from the 2017 International Conference on Silicon Carbide and related materials, September 17-22, 2017, Washington, DC, USA 2018 / p. 862-865 : ill <https://doi.org/10.4028/www.scientific.net/MSF.924.862> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; Land, Raul; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill
<https://doi.org/10.4028/www.scientific.net/MSF.897.697>

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

Korolkov, Oleg; Land, Raul; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 42

Some comparative properties of diffusion-welded contacts to 6H and 4H silicon carbide

Korolkov, Oleg; Rang, Toomas Silicon Carbide and Related Materials 2001 : ICSCRM2001 : proceedings of the International Conference on Silicon Carbide and Related Materials 2001, Tsukuba, Japan, October 28 - November 2, 2001. Part 2 2002 / p. 941-944 : ill

Some of comparative properties of diffusion welded contacts to 6H- and 4H-silicon carbide

Korolkov, Oleg; Rang, Toomas International Conference on Silicon Carbide and Related Materials 2001 - ICSCRM2001 - October 28-November 2, 2001 (Epochal Tsukuba, Ibaraki, Japan) : technical digest 2001 / p. 625-626 : ill

Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe

Mizsei, Janos; **Korolkov, Oleg; Toompuu, Jana; Rang, Toomas** The 9th European Conference on Silicon Carbide and Related Materials : abstract book : St. Petersburg Russia, 2-6 September, 2012 2012 / 2 p. : ill

Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe

Mizsei, Janos; **Korolkov, Oleg; Toompuu, Jana; Mikli, Valdek; Rang, Toomas** Silicon Carbide and Related Materials 2012 : selected peer reviewed papers from the 9th European Conference on Silicon Carbide and Related Materials (ECSCRM 2012), September 2-6, 2012, St. Petersburg, Russian Federation 2013 / p. 677-680 : ill

Subcontact layers in LPE structures for forming the ohmic contacts on GaAs semiconductor substrates

Korolkov, Oleg; Voitovitš, Viktor; Rang, Toomas Abstract book of 13th American Conference on Crystal Growth and Epitaxy : August 12-16, 2001, Burlington, Vermont, USA 2001 / p. 133

The basic parameters of diffusion welded Al Schottky contacts to p- and n-SiC

Korolkov, Oleg; Ruut, Jana; Kuznetsova, Natalja; Rang, Toomas Silicon Carbide and Related Materials 2003 2004 / p. 857-860
<https://doi.org/10.4028/www.scientific.net/MSF.457-460.857>

The basic Schottky parameters for combined diffusion welded and sputter metal contacts

Kuznetsova, Natalja; Korolkov, Oleg; Rang, Toomas; Pikkov, Mihhail BEC 2006 : 2006 International Baltic Electronics Conference : Tallinn University of Technology, October 2-4, 2006, Tallinn, Estonia : proceedings of the 10th Biennial Baltic Electronics Conference 2006 / p. 47-50 : ill

The dependence of reverse recovery time on barrier capacitance and series on-resistance in Schottky diodes

Veher, Oleksandr; Sleptšuk, Natalja; Toompuu, Jana; Korolkov, Oleg; Rang, Toomas Materials and contact characterisation VIII 2017 / p. 15-22 : ill <http://dx.doi.org/10.2495/MC170021>

The diffusion welded contacts in power electronics

Korolkov, Oleg; Rang, Toomas BEC : Baltic Electronics Conference : proceedings of the 4th Biennial Conference, October 9-14, 1994, Tallinn (Estonia). 2 1994 / p. 573-578: ill

The diffusion welded contacts in power electronics and electrotechnics

Korolkov, Oleg Telekommunikatsioon '98 : rahvusvahelise telekommunikatsioonipäeva konverentsi ettekannete materjalid, 15. mai 1998 1998 / lk. 84-86: ill

The measurement and tuning of SiC diode voltage doubler represented as diffusion-welded stack [Online resource]

Toompuu, Jana; Sleptšuk, Natalja; Land, Raul; Korolkov, Oleg; Rang, Toomas BEC 2018 : 2018 16th Biennial Baltic Electronics Conference (BEC) : proceedings of the 16th Biennial Baltic Electronics Conference, October 8-10, 2018 2018 / 4 p.: ill
<https://doi.org/10.1109/BEC.2018.8600963>

The Schottky parameter test for combined diffusion welded and sputter large area contacts

Korolkov, Oleg; Kuznetsova, Natalja; Rang, Toomas; Syrkin, A.; Dmitriev, V. Silicon carbide and related materials 2007 / p. 737-740 <https://www.scientific.net/MSF.556-557.737>

The specificity of solid-phase interaction of aluminium with silicon carbide in the manufacture of diffusion-welded contacts to semiconductor devices

Sleptšuk, Natalja; Korolkov, Oleg; Toompuu, Jana; Rang, Toomas; Mikli, Valdek Elektronika ir elektrotehnika = Electronics and electrical engineering 2012 / p. 45-48 : ill <https://eejournal.ktu.lt/index.php/elt/article/view/2610>

Анализ процессов распространения тепла в структурах импульсных силовых приборов вблизи плоскостей спая кремниевых пластин в высоковольтные "столбы"

Glazov, Aleksei; **Korolkov, Oleg** Известия высших учебных заведений. Материалы электронной техники 2012 / с. 65-69 : ил

Исследование р-п-переходов на основе 4H-SiC, изготовленных имплантацией бора, методом нестационарной емкостной спектроскопии

Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg; Sleptšuk, Natalja** Физика и техника полупроводников 2011 / с. 1358-1362 : ил

Низкотемпературный отжиг слаболегированных слоев n-4H-SiC после облучения быстрыми электронами

Korolkov, Oleg; Kozlovski, Vitali; Lebedev, Alexander; Sleptšuk, Natalja; Toompuu, Jana; Rang, Toomas Физика и техника полупроводников 2019 / с. 991-994 <https://doi.org/10.21883/FTP.2019.07.47879.9089>